

Weight

TO-247

TO-268

Advance Technical Information

GenX3[™] 1400V IGBTs w/ Diode

IXGH20N140C3H1 IXGT20N140C3H1

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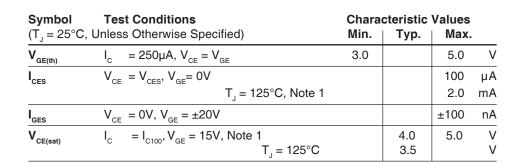
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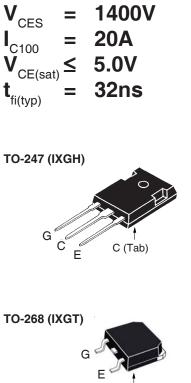
g

g

High-Speed PT IGBTs for 20 - 50 kHz Switching

	C		OE
Symbol	Test Conditions	Maximum F	Ratings
V _{CES}	T _{_1} = 25°C to 150°C	1400	V
	$T_{J} = 25^{\circ}C$ to 150°C, $R_{GE} = 1M\Omega$	1400	V
V _{GES}	Continuous	±20	V
V _{GEM}	Transient	±30	V
C25	$T_c = 25^{\circ}C$	42	A
C100	$T_c = 100^{\circ}C$	20	А
СМ	$T_c = 25^{\circ}C$, 1ms	108	A
A	$T_c = 25^{\circ}C$	20	A
AS	$T_{c}^{\circ} = 25^{\circ}C$	400	mJ
SSOA	$V_{ge} = 15V, T_{J} = 125^{\circ}C, R_{g} = 5\Omega$	I _{CM} = 40	А
RBSOA)	Clamped Inductive Load	$V_{CE} \le V_{CES}$	
)	$T_{c} = 25^{\circ}C$	250	W
Г,		-55 +150	°C
Г _{ЈМ}		150	°C
stg		-55 +150	°C
г,	1.6mm (0.062 in.) from Case for 10s	300	°C
	Plastic Body for 10 seconds	260	°C
M _d	Mounting Torque (TO-247)	1.13/10	Nm/lb.in.





C (Tab)

G = Gate = Collector С E = Emitter Tab = Collector

Features

- Optimized for Low Switching Losses
- Square RBSOA
- High Avalanche Capability
- Anti-Parallel Ultra Fast Diode
- International Standard Packages

Advantages

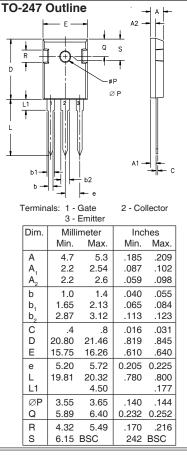
- High Power Density
- Low Gate Drive Requirement

Applications

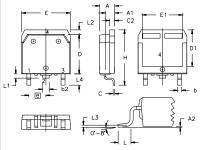
- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

		XYS						
Symbol Test Conditions			Characteristic Values					
$(T_{J} = 2$	5°C, l	Unless Otherwise Specified)	Min.	Тур.	Max.			
g _{fs}		$I_{c} = I_{c100}, V_{ce} = 10V, Note 1$	10	17	S			
C _{ies})			1790	pF			
C _{oes}	}	$V_{ce} = 25V, V_{ge} = 0V, f = 1MHz$		145	pF			
C _{res}	J			50	pF			
Q _g)			88	nC			
\mathbf{Q}_{ge}	}	$I_{c} = I_{c100}, V_{GE} = 15V, V_{CE} = 0.5 \bullet V_{CES}$		18	nC			
Q _{gc}	J			30	nC			
t _{d(on)}	١			19	ns			
t _{ri}		Inductive load, T _J = 25°C		12	ns			
E _{on}		$I_{c} = I_{c100}, V_{GE} = 15V$		1.35	mJ			
t _{d(off)}	($V_{CE} = 0.5 \bullet V_{CES}, R_G = 5\Omega$		110	ns			
t _{fi}		Note 2		32	ns			
E _{off}	J			0.44	0.80 mJ			
t _{d(on)})			22	ns			
t _{ri}		Inductive load, T _J = 125°C		13	ns			
E _{on}		$I_{c} = I_{c100}, V_{ge} = 15V$		2.33	mJ			
t _{d(off)}	($V_{CE} = 0.5 \bullet V_{CES}, R_G = 5\Omega$		144	ns			
t _{ri}		Note 2		380	ns			
E _{off})			1.64	mJ			
$\mathbf{R}_{_{\mathrm{thJC}}}$					0.50 °C/W			
R _{thCK}		TO-247		0.21	°C/W			

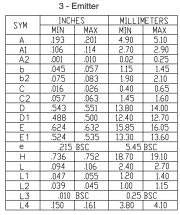
IXGH20N140C3H1 IXGT20N140C3H1



TO-268 Outline



Terminals: 1 - Gate 2 & 4 - Collector



Reverse Diode (FRED)

Symbol $(T_J = 25)$	I Test Conditions 5°C, Unless Otherwise Specified)	Char Min.	acteristic Values Typ. Max.			
V _F	$I_{_{\rm F}}$ = 20A, $V_{_{ m GE}}$ = 0V, Note 1 $T_{_{ m J}}$ = 125°C		2.8	3.0 V V		
I _{RM}	$I_{\rm F} = 20$ A, $V_{\rm GE} = 0$ V,		19	A		
t _{rr}	$\int -di_{\rm F}/dt = 750 {\rm A}/{\rm \mu s}, V_{\rm R} = 800 {\rm V}$		70	ns		
$\mathbf{R}_{_{\mathrm{thJC}}}$				0.9 °C/W		

Notes:

- 1. Pulse test, t \leq 300µs, duty cycle, d \leq 2%.
- 2. Switching times & energy losses may increase for higher V_{CF} (Clamp), T₁ or R₆.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits,	Test Conditions, and Dimensions.
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IXYS MOSFETs and IGBTs are covered	//	//-	- , ,	- , - , -	-, - ,	6,404,065 B1	- / / -	- , , ,		, . ,
by one or more of the following U.S. patents	: 4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,10		5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	2 7,071,537	



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